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FEATURES

RS1AA~RS1MA are available in SMA Package

- · For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- · Easy to pick and place
- · Fast reverse recovery time.
- Lead free in comply with EU RoHS 2011/65/EU directives

MECHANICAL DATA

· Case: SMA

 Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.055g / 0.002oz

ORDERING INFORMATION

Package Type	Part Number			
SMA	RS1AA			
	RS1BA			
	RS1DA			
	RS1GA			
	RS1JA			
	RS1KA			
	RS1MA			
SPQ	5,000pcs/Reel			
AiT provides all RoHS Compliant Products				

PIN DESCRIPTION



2

SMA Package



PIN#	DESCRIPTION
1	Cathode
2	Anode

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise specified.

Parameter	Symbols	RS1AA	RS1BA	RS1DA	RS1GA	Unit
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	100	200	400	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	V
Maximum Average Forward Rectified Current at T _c = 125 °C	I _{F(AV)}	1			Α	
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	IFSM	30				Α
Maximum Forward Voltage at 1 A	V_{F}	1.3			V	
Maximum DC Reverse Current TA = 25 °C at Rated DC Blocking Voltage TA =125 °C	I _R	5 50			μΑ	
Typical Junction Capacitance at V _R =4V, f=1MHz	C₃	15				pF
Maximum Reverse Recovery Time(1)	t _{rr}		1	50		ns
Typical Thermal Resistance ⁽²⁾	R _{θJA}	75				°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 ~ + 150			°C	
Parameter	Symbols	RS1JA	RS	1KA	RS1MA	Unit
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	600	80	00	1000	V
Maximum RMS voltage	V _{RMS}	420	50	60	700	V
IVIAAIITIUITI TXIVIO VOILAYE	VINIO					1/
Maximum DC Blocking Voltage	VDC	600	80	00	1000	V
-		600		1	1000	A
Maximum DC Blocking Voltage Maximum Average Forward Rectified Current	V _{DC}	600	, ,		1000	
Maximum DC Blocking Voltage Maximum Average Forward Rectified Current at T _c = 125 °C Peak Forward Surge Current 8.3 ms Single Half	V _{DC}	600	3	1	1000	А
Maximum DC Blocking Voltage Maximum Average Forward Rectified Current at T _c = 125 °C Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	V _{DC} $I_{F(AV)}$ I_{FSM}	600	3	1 80	1000	A A
Maximum DC Blocking Voltage Maximum Average Forward Rectified Current at T _c = 125 °C Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load Maximum Forward Voltage at 1 A Maximum DC Reverse Current TA = 25 °C	V _{DC} I _{F(AV)} I _{FSM} V _F	600	1 5	1 60 .3	1000	A A V
Maximum DC Blocking Voltage Maximum Average Forward Rectified Current at T _c = 125 °C Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load Maximum Forward Voltage at 1 A Maximum DC Reverse Current TA = 25 °C at Rated DC Blocking Voltage TA =125 °C Typical Junction Capacitance	VDC I _{F(AV)} I _{FSM} VF I _R	250	1 5	3 .3	1000	A A V μA
Maximum DC Blocking Voltage Maximum Average Forward Rectified Current at T _c = 125 °C Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load Maximum Forward Voltage at 1 A Maximum DC Reverse Current TA = 25 °C at Rated DC Blocking Voltage TA =125 °C Typical Junction Capacitance at V _R =4V, f=1MHz	VDC IF(AV) IFSM VF IR CJ		3 1	1 .3 .5 .60	1000	A A V µA pF

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

⁽¹⁾ Measured with IF = 0.5 A, I_R = 1 A, Irr = 0.25 A.

^(2) P.C.B. mounted with 1.0 X 1.0" (2.54 X 2.54 cm) copper pad areas.

TYPICAL CHARACTERISTICS

Fig 1. Forward Current Derating Curve

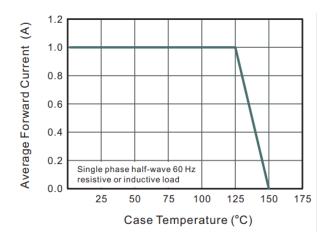


Fig 3. Typical Instantaneous Forward Characteristics

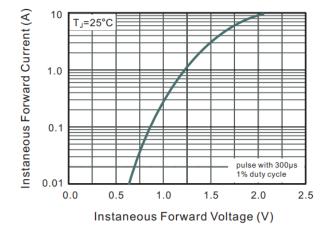


Fig 2. Typical Reverse Characteristics

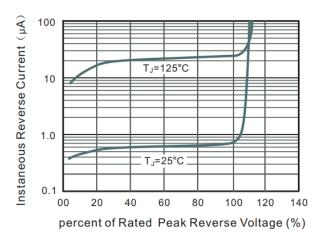


Fig 4. Typical Junction Capacitance

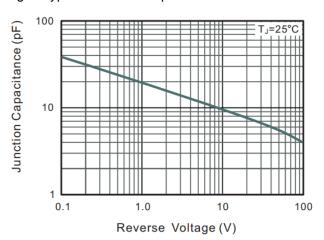
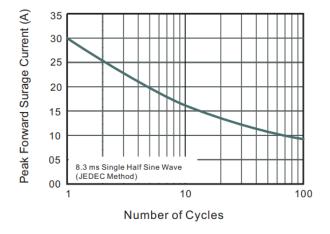


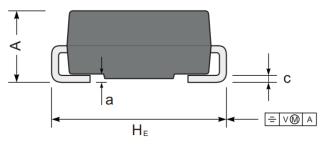
Fig 5. Maximum Non-Repetitive Peak Forward Surge Current

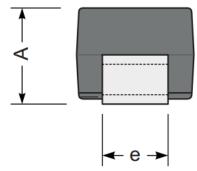


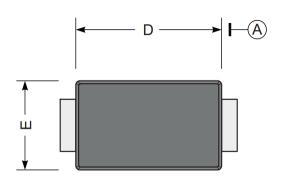


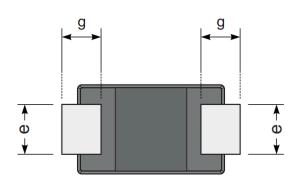
PACKAGE INFORMATION

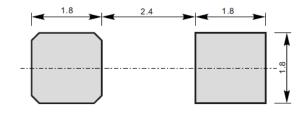
Dimension in SMA Package (Unit: mm)











Recommended Mounting Pad Size

Symbol	Min	Max	
А	1.9	2.45	
D	4.0	4.5	
Е	2.5	2.8	
HE	4.7	5.2	
С	0.15	0.31	
е	1.3	1.8	
g	0.9	1.5	
b	0.05	0.2	
а	0.3		

RS1AA_RS1MA

- 5 -

FAST RECOVERY RECTIFIER DIODE REVERSE VOLTAGE 50V TO 1000V FORWARD CURRENT 1A

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